

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	photodiode and cathode and anode and substrate and (monolithic monolithically) near integrated near vertical near2 photodiode and slightly near doped near2 epitaxial near layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:43
L2	0	photodiode and cathode and anode and substrate and (monolithic monolithically) near integrated near vertical near2 photodiode and slightly near doped and epitaxial near layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:43
L3	0	photodiode and cathode and anode and substrate and (monolithic monolithically) near integrated near vertical near2 photodiode and slightly near doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:43
L4	0	photodiode and cathode and anode and substrate and (monolithic monolithically) and vertical near2 photodiode and slightly near doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:43
L5	0	photodiode and cathode and anode and substrate and (monolithic monolithically) and vertical near2 photodiode and slightly near doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:44
L6	79	photodiode and cathode and anode and substrate and (monolithic monolithically) and vertical and doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:44

L7	0	photodiode and cathode and anode and substrate and (monolithic monolithically) and vertical and doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112") and "p.sup.-" and "n.sup.-"	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:48
L8	2	"p.sup.-" and "n.sup.-"	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:48
L9	1	photodiode and cathode and anode and substrate and (monolithic monolithically) and vertical and doped and epitaxial and layer and (@ad< "20021112" @rlad< "20021112") and lightly near doped near P-type and lightly near doped near n-type	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 13:50
L10	1	"5164813".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 14:00
L11	1	"6724018".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 14:26
S1	2	("4616247"   "6392383").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:45
S2	0	sahara.in. and pin near diode	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:47
S3	23	sahara.in. and pin and diode	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:47
S4	1	sahara.in. and pin and diode and (monolithic monolithically)	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:48
S5	0	pin near (photodiode diode) and (monolithic monolithically) and vertical and bimos and planar and slightly near dope near n- and epitaxial and (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:50
S6	4397603	pin near (photodiode diode) and (monolithic monolithically) (@ad< "20021112" @rlad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:51

S7	392	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:51
S8	330	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:51
S9	199	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:51
S10	30	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor and epitaxial and (back near side backside)	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:51
S11	1	"4616247".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:56
S12	25	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor and epitaxial and (back near side backside) and n-	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/20 23:59
S13	30	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor and epitaxial and (back near side backside)	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:09
S14	38	pin near (photodiode diode) and (monolithic monolithically) and (@ad< "20021112" @riad< "20021112") and substrate and semiconductor and (back near side backside)	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:09
S15	8	S14 not S13	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:10

S16	262	(pin p-i-n) near (photodiode diode) and (monolithic monolithically) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:14
S17	277	(pin p-i-n) near2 (photodiode diode) and (monolithic monolithically) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:14
S18	51	(pin p-i-n) near2 (photodiode diode) and (monolithic monolithically) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and epitaxial and backside	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:14
S19	2	(pin p-i-n) near (photodiode diode).ti. and (monolithic monolithically) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:19
S20	3	(pin p-i-n).ti. and (photodiode diode).ti. and (monolithic monolithically) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:21
S21	170	(pin p-i-n) near2 (photodiode diode) and (back near side backside) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and cathode and anode	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:24
S22	63	(pin p-i-n) near2 (photodiode diode) and (back near side backside) and (@ad<"20021112" @rlad<"20021112") and substrate and semiconductor and cathode and anode and epitaxial	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:24
S23	4397474	(pin p-i-n) near2 (photodiode diode) and n- near epitaxial near layer (@ad<"20021112" @rlad<"20021112")	US-PGPUB; USPAT; USOCR	OR	ON	2008/12/21 00:32

S24	34	(pin p-i-n) near2 (photodiode diode) and n- near epitaxial near layer and (@ad< "20021112" @rlad< "20021112")	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 00:32
S25	1	"4616247".pn. and "16"	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 01:54
S26	1	PIn near photodiode and p-near epitaxial same n- near epitaxial	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 01:59
S27	0	PIn near photodiode and p-near epitaxial same n- near epitaxial and (@ad< "20021112" @rlad< "20021112")	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 01:59
S28	406	PIn near photodiode and p near2 layer same n- near2 layer and (@ad< "20021112" @rlad< "20021112")	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 02:00
S29	122	PIn near photodiode and i near (layer zone) and p near2 layer same n- near2 layer and (@ad< "20021112" @rlad< "20021112")	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 02:01
S30	5	PIn near photodiode and i near (layer zone) same combination same p near2 layer same n- near2 layer and (@ad< "20021112" @rlad< "20021112")	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 02:04
S31	2	PIn near photodiode and i near (layer zone) same combination same p near2 layer same n- near2 layer and (@ad< "20021112" @rlad< "20021112") and (257/458,656,e29.226.ccls.357/30)	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 02:25
S32	85	PIn near photodiode and p near2 layer same n- near2 layer and (@ad< "20021112" @rlad< "20021112") and (257/458,656,e29.226.ccls.357/30)	US-PGRUB; USPAT; USOCR	OR	ON	2008/12/21 10:52

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